

TOSHIBA Field Effect Transistor Silicon P Channel MOS Type

# SSM3J01F

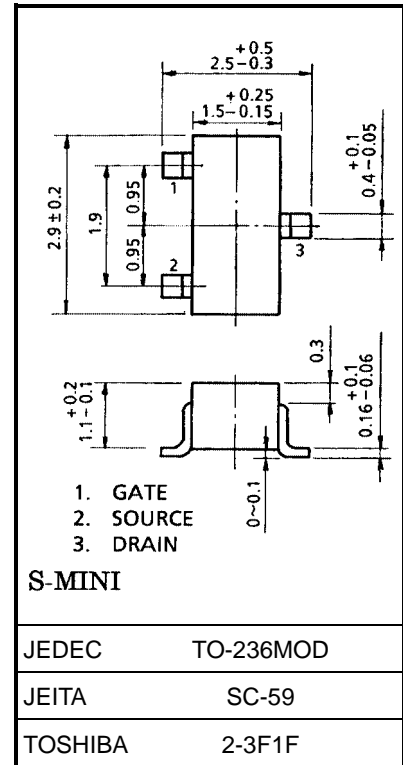
## High Speed Switching Applications

- Small package
- Low on resistance:  $R_{on} = 0.4 \Omega$  (max) ( $V_{GS} = -4 V$ )  
:  $R_{on} = 0.6 \Omega$  (max) ( $V_{GS} = -2.5 V$ )
- Low gate threshold voltage

## Maximum Ratings ( $T_a = 25^\circ C$ )

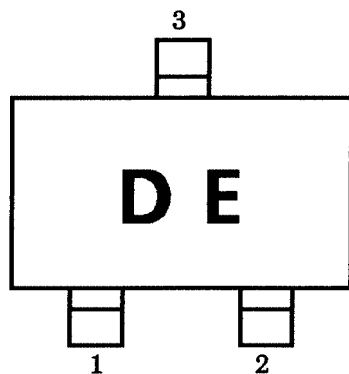
Characteristics		Symbol	Rating	Unit
Drain-source voltage		$V_{DS}$	-30	V
Gate-source voltage		$V_{GSS}$	$\pm 10$	V
Drain current	DC	$I_D$	-700	mA
	Pulse	$I_{DP}$	-1400	
Drain power dissipation ( $T_a = 25^\circ C$ )		$P_D$	200	mW
Channel temperature		$T_{ch}$	150	$^\circ C$
Storage temperature range		$T_{stg}$	-55~150	$^\circ C$

Unit: mm

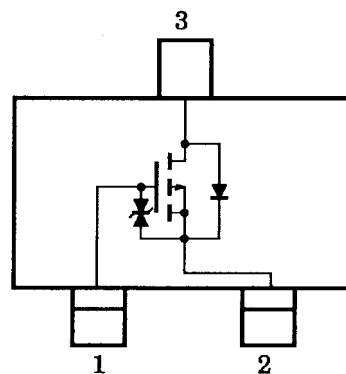


Weight: 0.012 g (typ.)

## Marking



## Equivalent Circuit



## Handling Precaution

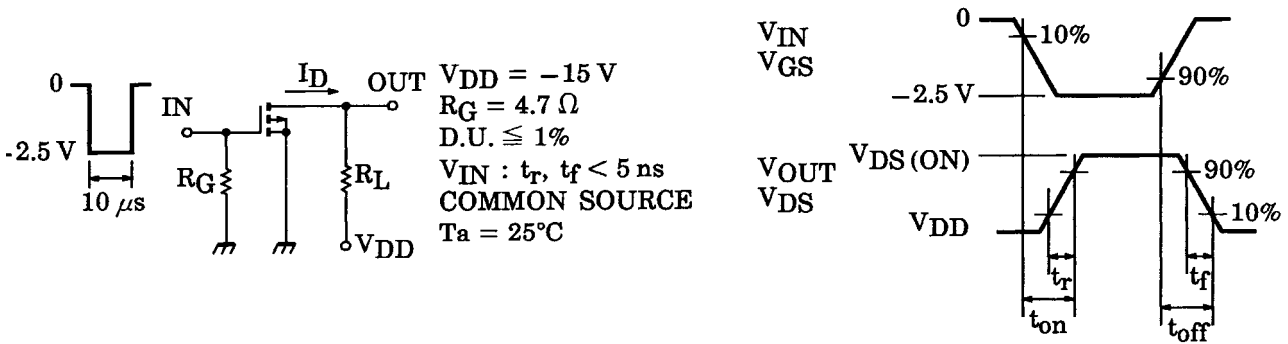
When handling individual devices (which are not yet mounting on a circuit board), be sure that the environment is protected against electrostatic electricity. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

**Electrical Characteristics (Ta = 25°C)**

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current	$I_{GSS}$	$V_{GS} = \pm 10\text{ V}, V_{DS} = 0$	—	—	$\pm 1$	$\mu\text{A}$
Drain-source breakdown voltage	$V_{(BR)DSS}$	$I_D = -1\text{ mA}, V_{GS} = 0$	-30	—	—	V
Drain cut-off current	$I_{DSS}$	$V_{DS} = -30\text{ V}, V_{GS} = 0$	—	—	-1	$\mu\text{A}$
Gate threshold voltage	$V_{th}$	$V_{DS} = -3\text{ V}, I_D = -0.1\text{ mA}$	-0.6	—	-1.1	V
Forward transfer admittance	$ Y_{fs} $ (Note)	$V_{DS} = -3\text{ V}, I_D = -0.35\text{ A}$	1.0	—	—	S
Drain-source ON resistance	$R_{DS(ON)}$ (Note)	$I_D = -0.35\text{ A}, V_{GS} = -4\text{ V}$	—	0.3	0.4	$\Omega$
		$I_D = -0.35\text{ A}, V_{GS} = -2.5\text{ V}$	—	0.4	0.6	
Input capacitance	$C_{iss}$	$V_{DS} = -10\text{ V}, V_{GS} = 0, f = 1\text{ MHz}$	—	240	—	pF
Reverse transfer capacitance	$C_{rss}$	$V_{DS} = -10\text{ V}, V_{GS} = 0, f = 1\text{ MHz}$	—	24	—	pF
Output capacitance	$C_{oss}$	$V_{DS} = -10\text{ V}, V_{GS} = 0, f = 1\text{ MHz}$	—	94	—	pF
Switching time	Turn-on time	$V_{DD} = -15\text{ V}, I_D = -0.3\text{ A},$ $V_{GS} = 0 \sim -2.5\text{ V}, R_G = 4.7\text{ }\Omega$	—	36	—	ns
	Turn-off time		—	37	—	

Note: Pulse test

**Switching Time Test Circuit**



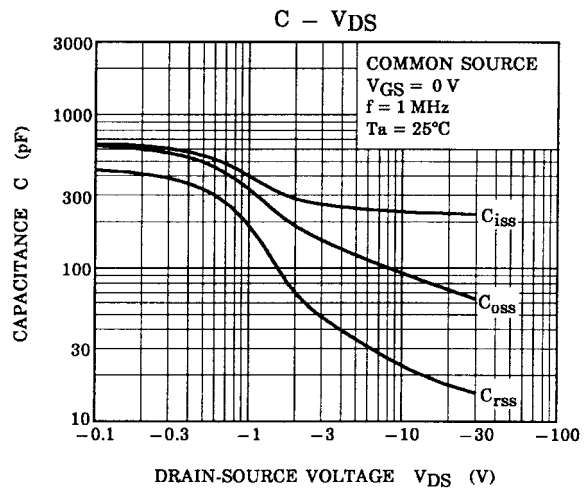
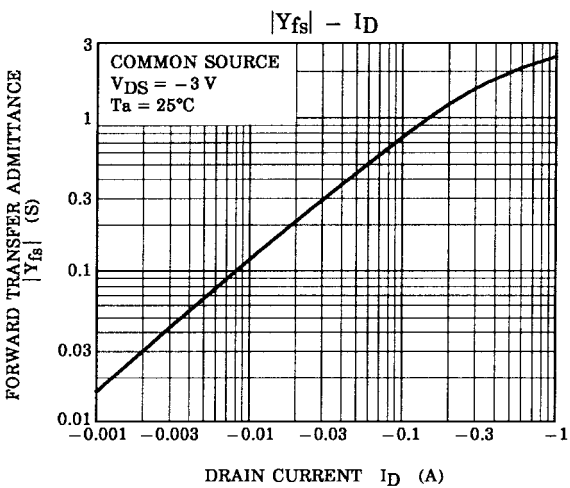
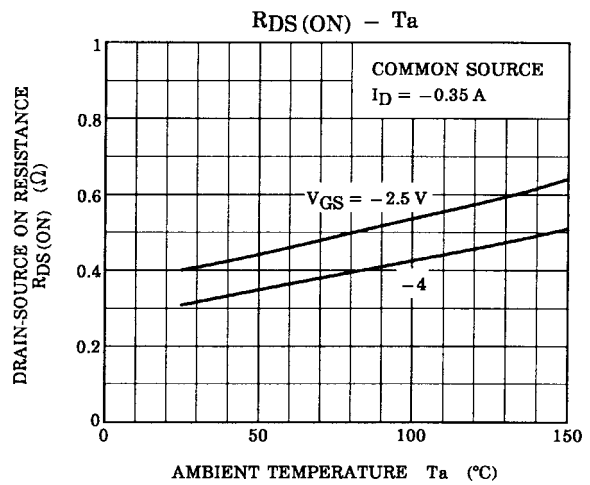
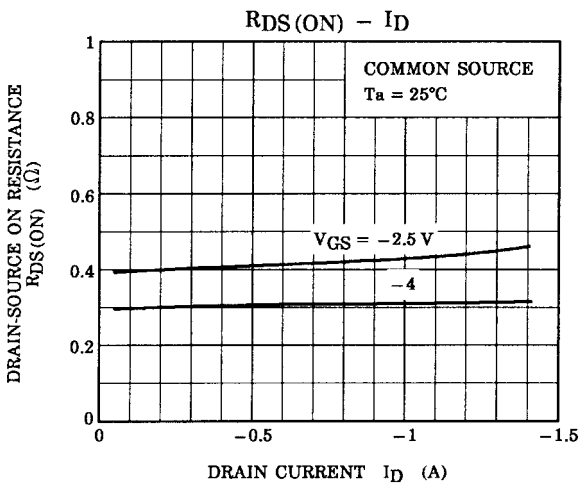
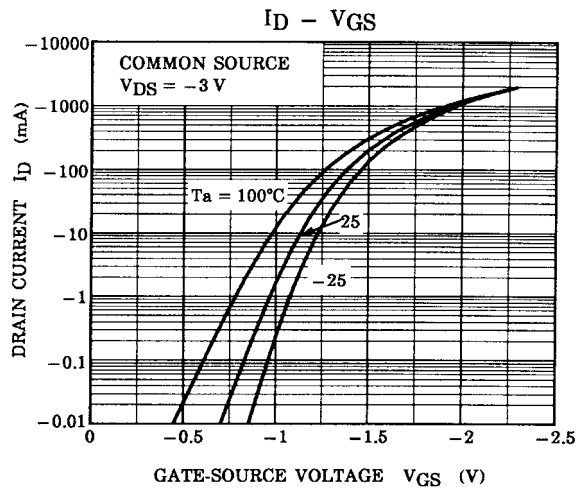
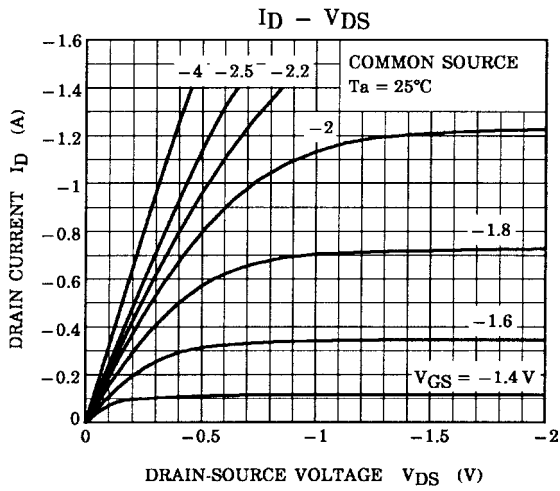
**Precaution**

$V_{th}$  can be expressed as voltage between gate and source when low operating current value is  $I_D = -100\text{ }\mu\text{A}$  for this product. For normal switching operation,  $V_{GS(ON)}$  requires higher voltage than  $V_{th}$  and  $V_{GS(off)}$  requires lower voltage than  $V_{th}$ .

(Relationship can be established as follows:  $V_{GS(off)} < V_{th} < V_{GS(ON)}$ )

Please take this into consideration for using the device.

$V_{GS}$  recommended voltage of  $-2.5\text{ V}$  or higher to turn on this product.



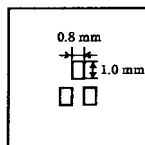
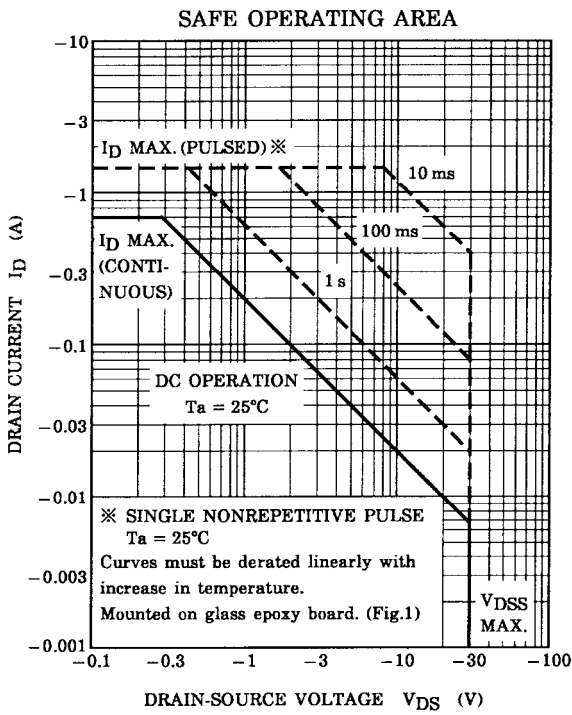
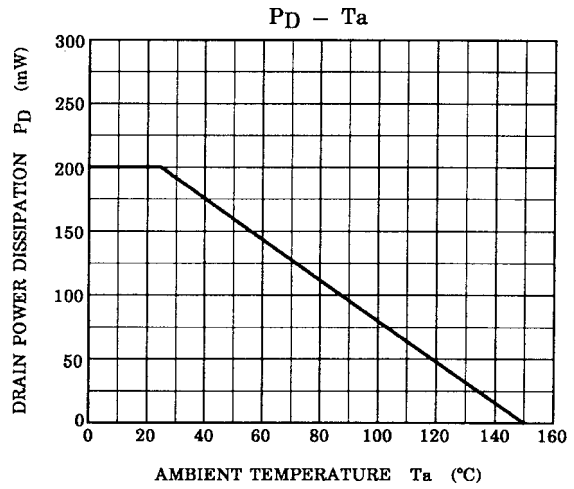
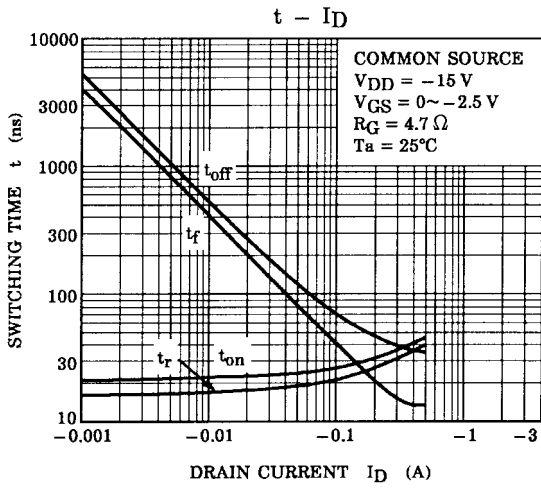


Figure 1 25.4 mm × 25.4 mm × 1.6 t (a Cu pad of 0.8 mm<sup>2</sup> area)

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